

XP223N10013R-G

ETR11077-001

N-channel MOSFET 20V, 1A

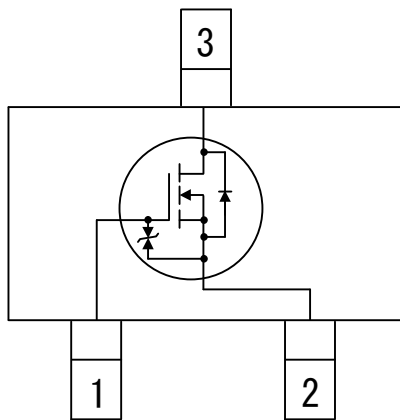
FEATURES

On-State Resistance : $R_{DS(on)} = 0.3\Omega @ V_{GS} = 4.5V$
Driving voltage : 1.5V
Environmentally Friendly : EU RoHS Compliant, Pb Free

APPLICATIONS

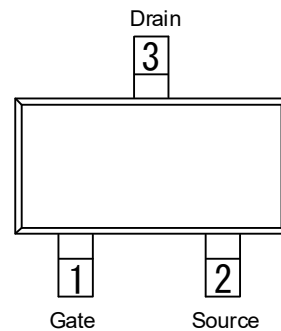
● Switching

EQUIVALENT CIRCUIT



PIN CONFIGURATION

● SOT-323-3A



PRODUCT NAME

PRODUCT NAME	PACKAGE	ORDER UNIT
XP223N10013R-G *	SOT-323-3A	3,000pcs/ Reel

* The "-G" suffix denotes Halogen and Antimony free as well as being fully EU RoHS compliant

ABSOLUTE MAXIMUM RATINGS

$T_a = 25^\circ\text{C}$

PARAMETER	SYMBOL	RATINGS	UNITS
Drain-Source Voltage	V_{DS}	20	V
Gate-Source Voltage	V_{GS}	± 8	V
Drain Current (DC)	I_D	1	A
Drain Current(Pulse) ^(*)	I_{DP}	2	A
Channel Power Dissipation ^(*)	P_d	0.35	W
Junction Temperature	T_J	150	$^\circ\text{C}$
Storage Temperature	T_{stg}	-55~150	$^\circ\text{C}$

^(*) $PW \leq 10\mu\text{s}$, duty cycle $\leq 1\%$

^(*) When implemented on a PCB defined by JESD51-7

ELECTRICAL CHARACTERISTICS

Ta=25°C

PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$I_D = 100\mu A, V_{GS} = 0V$	20	-	-	V
Drain-Source Leakage Current	I_{DSS}	$V_{DS} = 20V, V_{GS} = 0V$	-	-	1	μA
Gate-Source Leakage Current	I_{GSS}	$V_{GS} = \pm 8V, V_{DS} = 0V$	-	-	± 10	μA
Gate Threshold Voltage	$V_{GS(off)}$	$I_D = 250\mu A, V_{DS} = V_{GS}$	0.4	0.8	1.2	V
Drain-Source On Resistance	$R_{DS(on)}$	$V_{GS} = 4.5V, I_D = 350mA$	-	0.15	0.3	Ω
		$V_{GS} = 2.5V, I_D = 350mA$	-	0.25	0.35	Ω
		$V_{GS} = 1.8V, I_D = 350mA$	-	0.4	1	Ω
		$V_{GS} = 1.5V, I_D = 20mA$	-	0.55	10	Ω
Input Capacitance	C_{iss}	$V_{DS} = 10V, V_{GS} = 0V$ $f = 1MHz$	-	99	-	pF
Output Capacitance	C_{oss}		-	20	-	pF
Reverse Transfer Capacitance	C_{rss}		-	13	-	pF
Turn-on Delay Time	$t_{d(on)}$	$V_{DD} = 10V, I_D = 500mA$ $V_{GS} = 4.5V$	-	8	-	ns
Rise Time	t_r		-	8	-	ns
Turn-off Delay Time	$t_{d(off)}$		-	26	-	ns
Fall Time	t_f		-	10	-	ns
Total Gate Charge	Q_g	$V_{DS} = 10V, I_D = 500mA$ $V_{GS} = 6V$	-	1.4	-	nC
Gate-Source Charge	Q_{gs}		-	0.14	-	nC
Gate-Drain Charge	Q_{gd}		-	0.36	-	nC
Diode Forward Voltage	V_{SD}	$I_S = 350mA, V_{GS} = 0V$	-	0.75	1.2	V

NOTES ON USE

1. Please use this IC within the absolute maximum ratings.

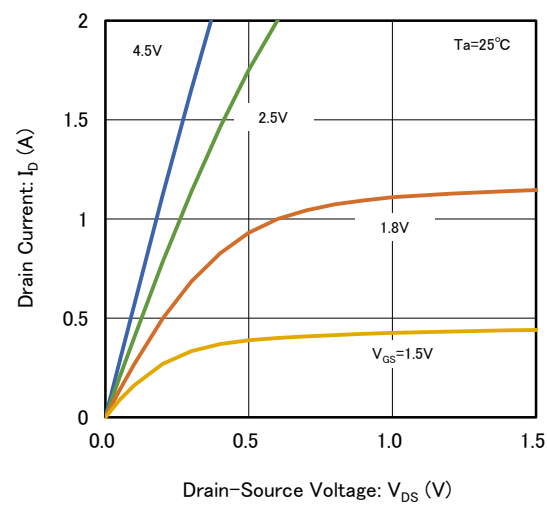
Even within the ratings, in case of high load use continuously such as high temperature, high voltage, high current and thermal stress may cause reliability degradation of the IC.

2. Torex places an importance on improving our products and their reliability.

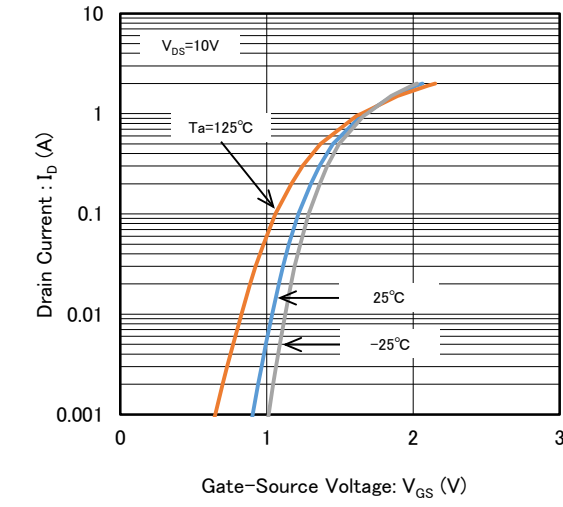
We request that users incorporate fail-safe designs and post-aging protection treatment when using Torex products in their systems.

■ TYPICAL PERFORMANCE CHARACTERISTICS

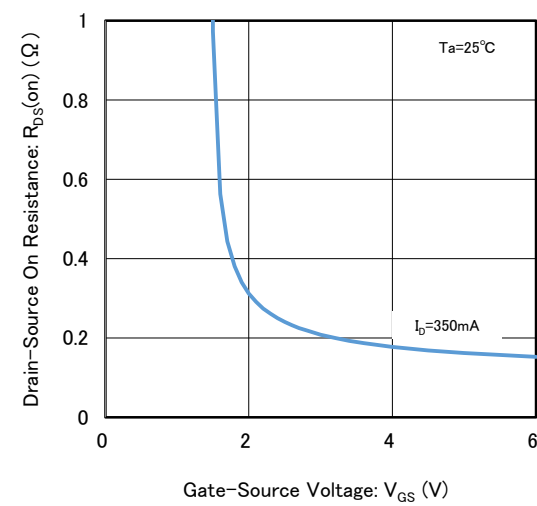
(1) Drain Current vs. Drain-Source Voltage



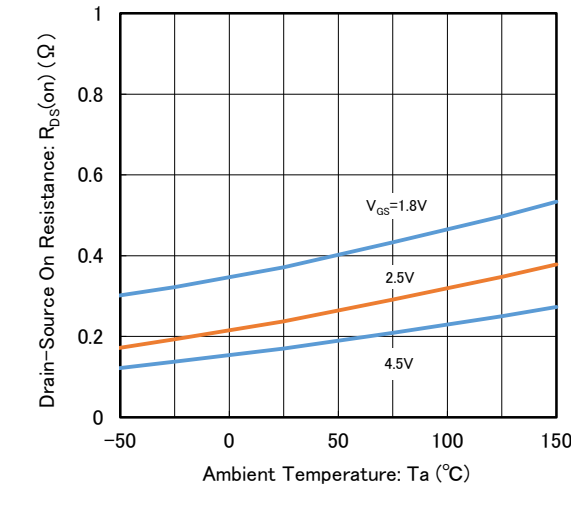
(2) Drain Current vs. Gate-Source Voltage



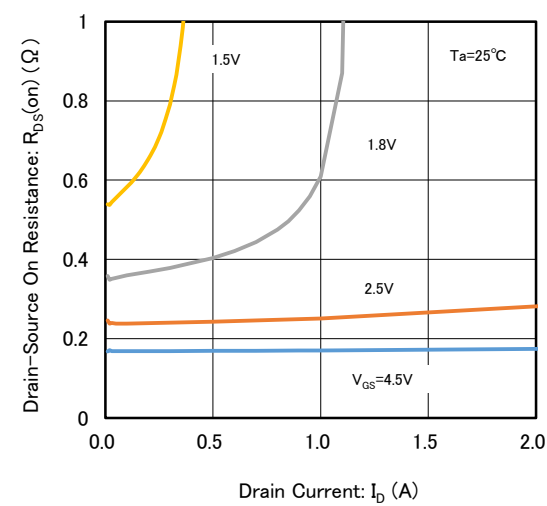
(3) Drain-Source On Resistance vs. Gate-Source Voltage



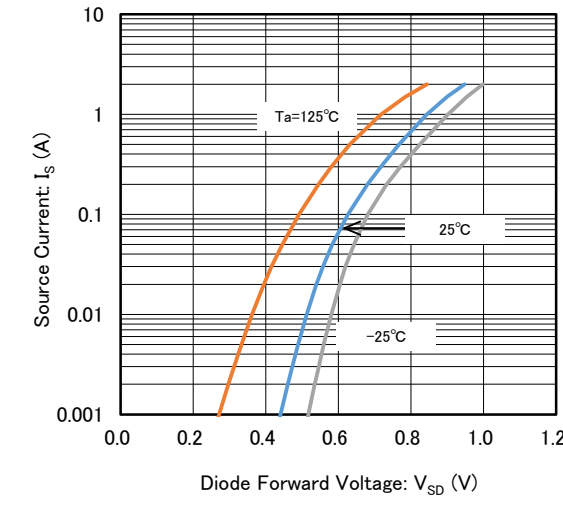
(4) Drain-Source On Resistance vs. Ambient Temperature



(5) Drain-Source On Resistance vs. Drain Current

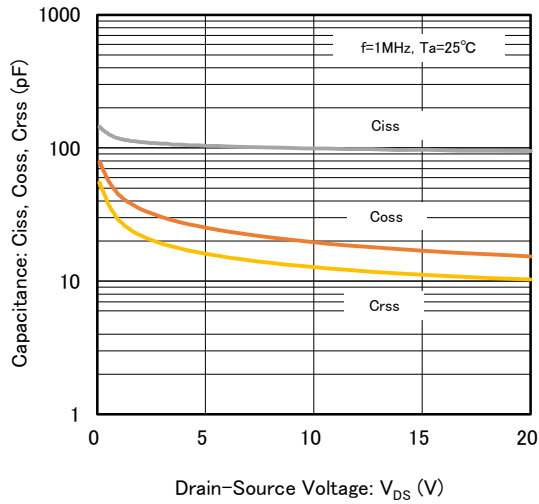


(6) Source Current vs. Diode Forward Voltage

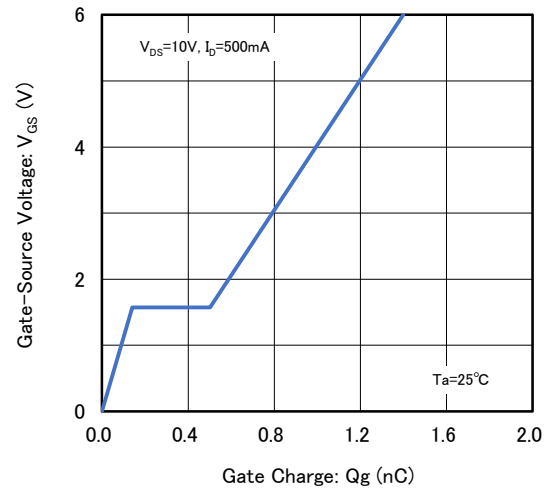


TYPICAL PERFORMANCE CHARACTERISTICS

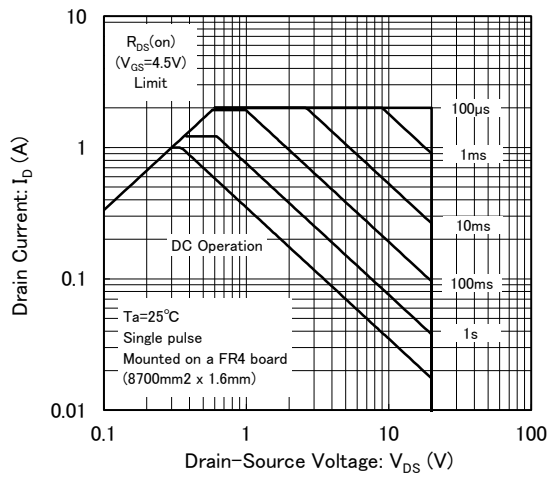
(7) Ciss, Coss, Crss vs. Drain-Source Voltage



(8) Gate-Source Voltage vs. Gate Charge



(9) Area of Safe Operation



■PACKAGING INFORMATION

For the latest package information go to, www.torexsemi.com/technical-support/packages

PACKAGE	OUTLINE / LAND PATTERN	THERMAL CHARACTERISTICS	
SOT-323-3A	SOT-323-3A PKG	JESD51-7 Board	SOT-323-3A Power Dissipation

■ MARKING RULE

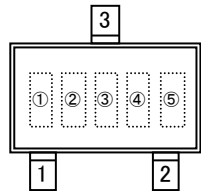
●SOT-323-3A

①,②,③represents product series

MARK			PRODUCT SERIES
①	②	③	
2	3	N	XP223N1001**-G

④,⑤ represents production lot number
01 to 09, 0A to 0Z, 11 to 9Z, A1 to A9, AA to AZ, B1 to ZZ repeated
(G, I, J, O, Q, W excluded) *No character inversion used

SOT-323-3A



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